2SC4262

Silicon NPN Epitaxial

HITACHI

Application

UHF / VHF Local oscillator

Outline

CMPAK



- 1. Emitter
- 2.Base
- 3. Collector



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Absolute Maximum Ratings ($Ta = 25^{\circ}C$)

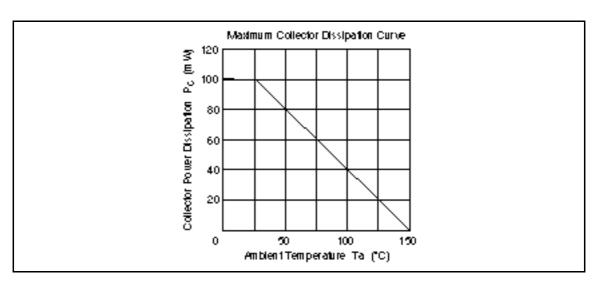
Item	Symbol	Ratings	Unit
Collector to base voltage	V_{CBO}	20	V
Collector to emitter voltage	V_{CEO}	15	V
Emitter to base voltage	V_{EBO}	3	V
Collector current	I _c	50	mA
Collector power dissipation	P _c	100	mW
Junction temperature	Tj	150	°C
Storage temperature	Tstg	-55 to +150	°C

Electrical Characteristics ($Ta = 25^{\circ}C$)

Item	Symbol	Min	Тур	Max	Unit	Test conditions
Collector to base breakdown voltage	$V_{(BR)CBO}$	20	_	_	V	$I_{\rm C} = 10 \; \mu A, \; I_{\rm E} = 0$
Collector to emitter breakdown voltage	$V_{(BR)CEO}$	15	_	_	V	$I_C = 1 \text{ mA}, R_{BE} =$
Collector cutoff current	I _{CBO}	_	_	0.5	μΑ	$V_{CB} = 15 \text{ V}, I_{E} = 0$
Emitter cutoff current	I _{EBO}	_	_	1.0	μΑ	$V_{EB} = 3 \text{ V}, I_{C} = 0$
Collector to emitter saturation voltage	$V_{\text{CE(sat)}}$	_	_	0.5	V	$I_{\rm C}$ = 20 mA, $I_{\rm B}$ = 4 mA
DC current transfer ratio	h _{FE}	50	_	200		$V_{CE} = 10 \text{ V}, I_{C} = 5 \text{ mA}$
Collector output capacitance	Cob	_	_	1.0	pF	$V_{CB} = 10 \text{ V}, I_{E} = 0, f = 1 \text{MHz}$
Gain bandwidth product	f _T	1.4	2.9	_	GHz	$V_{CE} = 10 \text{ V}, I_{C} = 5 \text{ mA}$

Note: Marking is "IP-".

See characteristic curves of 2SC3793.



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HITACHI

Hitachi, Ltd.
Semiconductor & IC Div.
Nippon Bidg., 2-6-2, Ohte-medii, Chiyode-ku, Tokyo 100, Jepen Tet Tokyo (03, 3270-2111
Fex: (03, 3270-5109)

For further in formellion write to: Hitachi Americe, Ltd. Semiconductor & IC Div. 2000 Sierre Point Perkwey Briebene, CA. 94005-4835 U.S.A. Tek AUS Sen 2000

Briebene, CA. 94005-1835 Damecher 3 U.S.A. D.85622 Fe Tet 445-589-8300 München Fex: 445-583-4207 Tet 089-9 9 Fex: 089-9 3

Hitachi Burope GmbH Bedronic Componente Group 6
Continentel Burope 1
Dornecher Streiße 3 V
0-85622 Feldkirchen L
München 1
Tet 08949 29 30 00 Fext 08949 29 30 00

Hitachi Burope Ltd.
Bedronie Componenta Div.
Northern Burope Headquerters
Whitebrook Ferk
Lower Cook ham Road
Maidenhead
Berkehire SL68YA
United Kingdom
Tet 0628-855000
Fex 0628-778322

Hitschi Asia Pte. Ltd 45 Collyer Quay \$20-00 Hitschi Tower Snappore 0404 Tat 535-2400 Fex: 535-4533

Hitachi Asia (Hong Kong) Ltd. Unit 705, North Towar, World Finance Centre, Herbour City, Centon Road Taim She Taul, Kowloon Hong Kong Tet 27350218 Fax: 27306074